

# Sebastian Walde

## List of Publications by Year in descending order

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Version: 2024-02-01

12  
papers

245  
citations

1040056

9  
h-index

1199594

12  
g-index

12  
all docs

12  
docs citations

12  
times ranked

220  
citing authors

#	ARTICLE	IF	CITATIONS
1	High-quality AlGaIn epitaxy on lattice-engineerable AlN template for high-power UVC light-emitting diodes. <i>Acta Materialia</i> , 2022, 226, 117625.	7.9	10
2	High-temperature Annealing and Patterned AlN/Sapphire Interfaces. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2100187.	1.5	12
3	Role of oxygen diffusion in the dislocation reduction of epitaxial AlN on sapphire during high-temperature annealing. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	12
4	Improving AlN Crystal Quality and Strain Management on Nanopatterned Sapphire Substrates by High-temperature Annealing for UVC Light-emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900796.	1.8	15
5	High-temperature Annealing of AlGaIn. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 2000473.	1.8	5
6	Reliability of UVC LEDs fabricated on AlN/sapphire templates with different threading dislocation densities. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	34
7	The Impact of AlN Templates on Strain Relaxation Mechanisms during the MOVPE Growth of UVB-LED Structures. <i>Crystal Research and Technology</i> , 2020, 55, 1900215.	1.3	6
8	Overcoming the excessive compressive strain in AlGaIn epitaxy by introducing high Si-doping in AlN templates. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 070904.	1.5	16
9	Status and Prospects of AlN Templates on Sapphire for Ultraviolet Light-emitting Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1901022.	1.8	34
10	Nanopatterned sapphire substrates in deep-UV LEDs: is there an optical benefit?. <i>Optics Express</i> , 2020, 28, 3619.	3.4	18
11	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. <i>Photonics Research</i> , 2020, 8, 589.	7.0	49
12	Impact of intermediate high temperature annealing on the properties of AlN/sapphire templates grown by metalorganic vapor phase epitaxy. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SC1002.	1.5	34